

HIGH POWER NPN SILICON TRANSISTOR

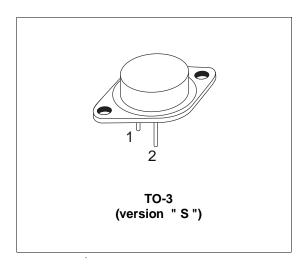
- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED
- HIGH RUGGEDNESS

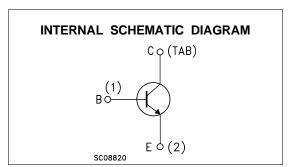
APPLICATION

- MOTOR CONTROL
- UNINTERRUPTABLE POWER SUPPLY

DESCRIPTION

The BUT100 is a Multiepitaxial Planar NPN Transistor in TO-3 package. It is intended for use in high frequency and efficency converters, switching regulators and motor control.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage (V _{BE} = -1.5V)	200	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0) 125		V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	7	V
lΕ	Emitter Current	50	А
I _{EM}	Emitter Peak Current	150	А
I _B	Base Current	10	А
I _{BM}	Base Peak Current	30	А
P _{tot}	Total Dissipation at T _c < 25 °C	300	W
T _{stg}	Storage Temperature	-65 to 200	°C
Tj	Max. Operating Junction Temperature	200	°C

February 2003

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	0.58	°C/W	
-----------------------	----------------------------------	-----	------	------	--

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

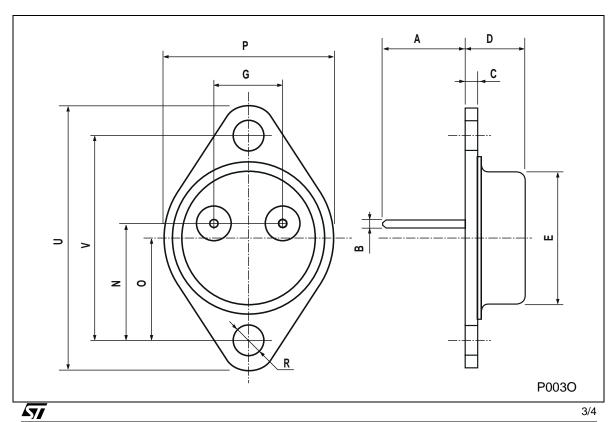
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CER}	Collector Cut-off Current ($R_{BE} = 5\Omega$)	V _{CE} = V _{CEV} V _{CE} = V _{CEV} T _C = 100°C			1 5	mA mA
I _{CEV}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = V _{CEV} V _{CE} = V _{CEV} T _C = 100°C			1 4	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 0.2 A L = 25mH	125			V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	I _E = 50mA	7			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$\begin{split} I_C &= 50 A & I_B = 2.5 A \\ I_C &= 100 A & I_B = 10 A \\ I_C &= 50 A & I_B = 2.5 A & T_c = 100^{\circ} C \\ I_C &= 100 A & I_B = 10 A & T_c = 100^{\circ} C \end{split}$			0.9 0.9 1.2 1.5	V V V
V _{BE} (sat)*	Base-Emitter Saturation Voltage	$\begin{split} I_C &= 50 A & I_B = 2.5 A \\ I_C &= 100 A & I_B = 10 A \\ I_C &= 50 A & I_B = 2.5 A & T_c = 100^{\circ} C \\ I_C &= 100 A & I_B = 10 A & T_c = 100^{\circ} C \end{split}$			1.4 2 1.4 2.1	V V V
di _c /dt	Rate of Rise of on-state Collector Current	$V_{CC} = 100V$ $R_C = 0$ $I_{B1} = 5A$ $T_p = 3\mu s$ $T_c = 100^{\circ}C$	180			A/μs
t _s t _f t _c	INDUCTIVE LOAD Storage time Fall Time Crossover Time	$\begin{array}{lll} V_{CC} = 90V & V_{clamp} = 125 \ V \\ I_{C} = 50A & I_{B1} = 2.5A \\ V_{BB} = -5V & L_{C} = 80 \mu H \\ R_{B2} = 1 \ \Omega & T_{c} = 100 ^{\circ} C \end{array}$			2 0.2 0.35	μs μs μs
VCEW	Maximum Collector Emitter Voltage without Snubber	$\begin{array}{ll} V_{CC} = 90V & I_{CWoff} = 150A \\ v_{BB} = -5V & I_{B1} = 10A \\ L_{C} = 30\mu H & R_{B2} = 1\Omega \\ T_{c} = 125^{\circ}C \end{array}$	125			V

^{*} Pulsed: Pulse duration = 3μs, duty cycle = 2 %

2/4

TO-3 (version S) MECHANICAL DATA

DIM.	mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	11.00		13.10	0.433		0.516
В	1.47		1.60	0.058		0.063
С	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
Е	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
Р	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2003 STMicroelectronics – Printed in Italy – All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com

4/4